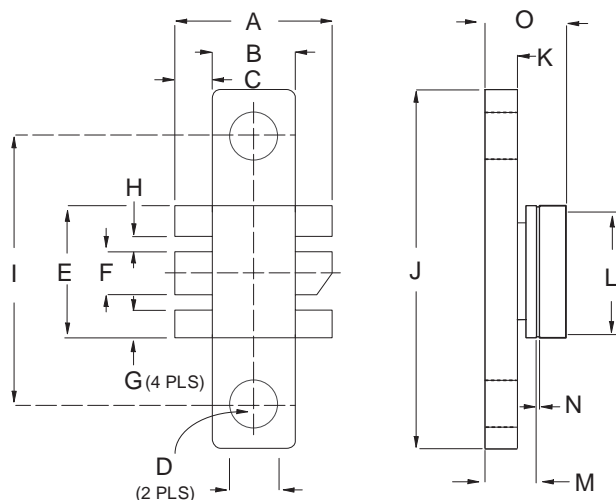


MECHANICAL DATA



SOT 171

PIN 1	SOURCE	PIN 2	SOURCE
PIN 3	GATE	PIN 4	DRAIN
PIN 5	SOURCE	PIN 6	SOURCE

DIM	mm	Tol.	Inches	Tol.
A	10.92	0.25	0.430	0.001
B	5.84	0.08	0.230	0.003
C	2.54	0.08	0.100	0.003
D	3.30 dia	0.13	0.130 dia	0.05
E	9.14	0.08	0.360	0.003
F	3.05	0.08	0.120	0.003
G	2.01	0.08	0.079	0.003
H	1.04	0.08	0.041	0.003
I	18.42	0.08	0.725	0.003
J	24.77	0.08	0.975	0.003
K	2.74	0.08	0.108	0.003
L	9.14	0.13	0.360	0.005
M	4.19	0.08	0.165	0.003
N	0.13	0.05	0.005	0.002
O	7.11	MAX	0.280	MAX

**GOLD METALLISED  
MULTI-PURPOSE SILICON  
DMOS RF FET  
20W – 28V – 500MHz  
SINGLE ENDED**

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND

APPLICATIONS

- VERY LOW  $C_{rss}$
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN – 11 dB MINIMUM

APPLICATIONS

- HF/VHF/UHF COMMUNICATIONS  
from 1 MHz to 1 GHz

ABSOLUTE MAXIMUM RATINGS ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

$P_D$	Power Dissipation	50W
$BV_{DSS}$	Drain – Source Breakdown Voltage	65V
$BV_{GSS}$	Gate – Source Breakdown Voltage	$\pm 20V$
$I_{D(sat)}$	Drain Current *	6A
$T_{stg}$	Storage Temperature	-65 to 150°C
$T_j$	Maximum Operating Junction Temperature	200°C

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

## ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub> Drain–Source Breakdown Voltage	V <sub>GS</sub> = 0 I <sub>D</sub> = 10mA	65			V
I <sub>DSS</sub> Zero Gate Voltage Drain Current	V <sub>DS</sub> = 28V V <sub>GS</sub> = 0			6	mA
I <sub>GSS</sub> Gate Leakage Current	V <sub>GS</sub> = 20V V <sub>DS</sub> = 0			6	μA
V <sub>GS(th)</sub> Gate Threshold Voltage *	I <sub>D</sub> = 10mA V <sub>DS</sub> = V <sub>GS</sub>	1		7	V
g <sub>fs</sub> Forward Transconductance *	V <sub>DS</sub> = 10V I <sub>D</sub> = 1.2A	1.08			S
G <sub>PS</sub> Common Source Power Gain	P <sub>O</sub> = 20W	11			dB
η Drain Efficiency	V <sub>DS</sub> = 28V I <sub>DQ</sub> = 0.6A	40			%
VSWR Load Mismatch Tolerance	f = 500MHz	20:1			—
C <sub>iss</sub> Input Capacitance	V <sub>DS</sub> = 0 V <sub>GS</sub> = -5V f = 1MHz			72	pF
C <sub>oss</sub> Output Capacitance	V <sub>DS</sub> = 28V V <sub>GS</sub> = 0 f = 1MHz			36	pF
C <sub>rss</sub> Reverse Transfer Capacitance	V <sub>DS</sub> = 28V V <sub>GS</sub> = 0 f = 1MHz			3	pF

\* Pulse Test: Pulse Duration = 300 μs , Duty Cycle ≤ 2%

## HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

**THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.**

## THERMAL DATA

R <sub>THj-case</sub>	Thermal Resistance Junction – Case	Max.3.5°C / W
-----------------------	------------------------------------	---------------

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

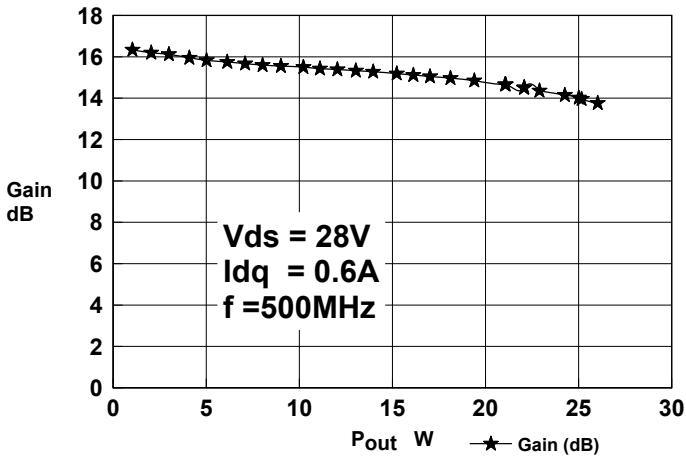


Figure 1- Gain vs. Power Output

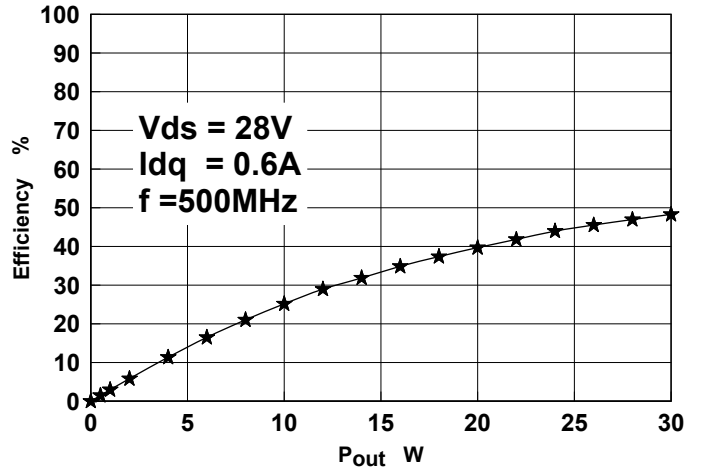


Figure 2 - Efficiency vs Power Output

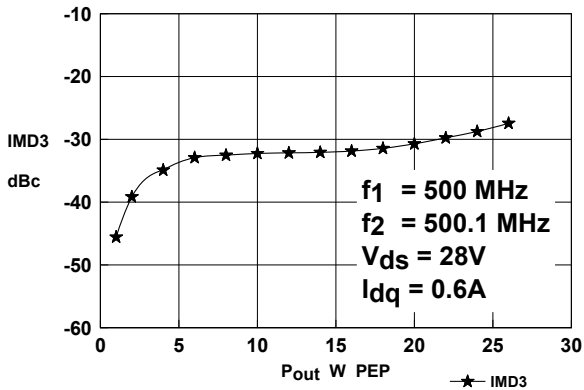


Figure 3 - IMD vs Power Output

### Typical S Parameters

! Vds=28V Idq=0.6A  
# MHz S MA R 50

!Freq !MHz	S11		S21		S12		S22	
	mag	ang	mag	ang	mag	ang	mag	ang
100	0.85	-155.5	15.46	87.8	0.017	-0.7	0.51	-144.5
200	0.86	-167.1	7.325	64.7	0.014	-12.0	0.6	-150.4
300	0.89	-171.2	4.597	50.7	0.012	-15.0	0.69	-155.0
400	0.91	-173.9	2.971	38.2	0.009	-13.0	0.77	-159.0
500	0.93	-177.1	2.155	29.7	0.006	5.7	0.82	-162.8
600	0.94	-179.6	1.634	17.6	0.006	29.4	0.86	-166.8
700	0.95	178.6	1.182	9.4	0.007	52.3	0.9	-169.2
800	0.96	176.6	0.7884	5.3	0.009	65.1	0.92	-172.7
900	0.97	174.7	0.6543	7.2	0.012	71.7	0.93	-175.0
1000	0.97	173.2	0.556	5.7	0.015	75.0	0.94	-176.6

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

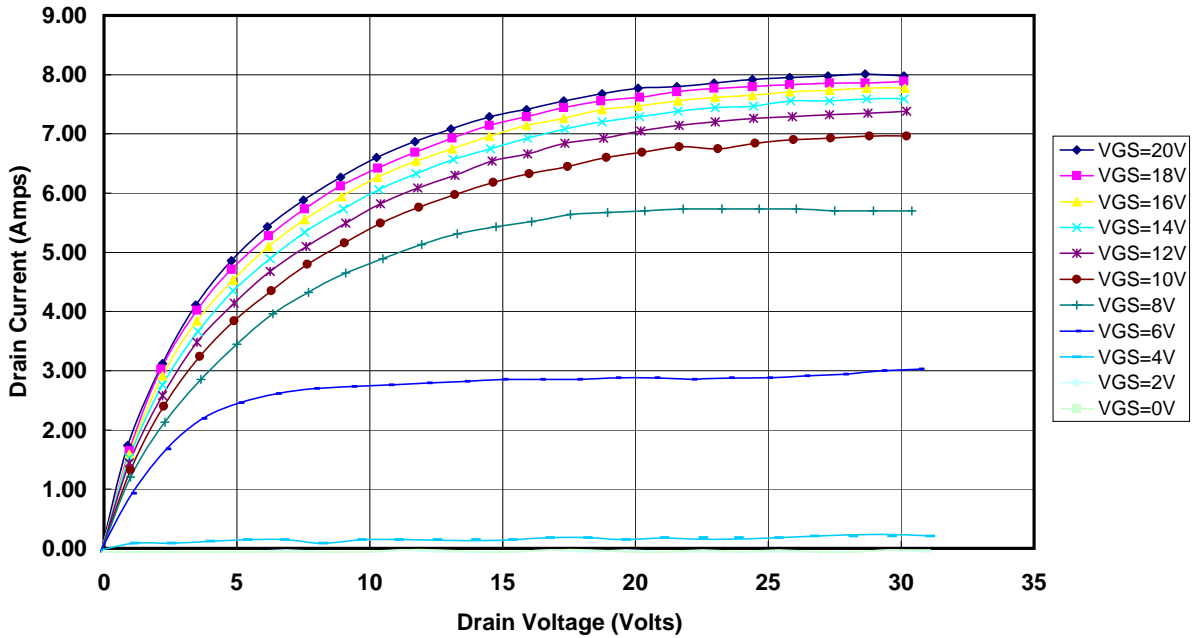


Figure 4 – Typical IV Characteristics.

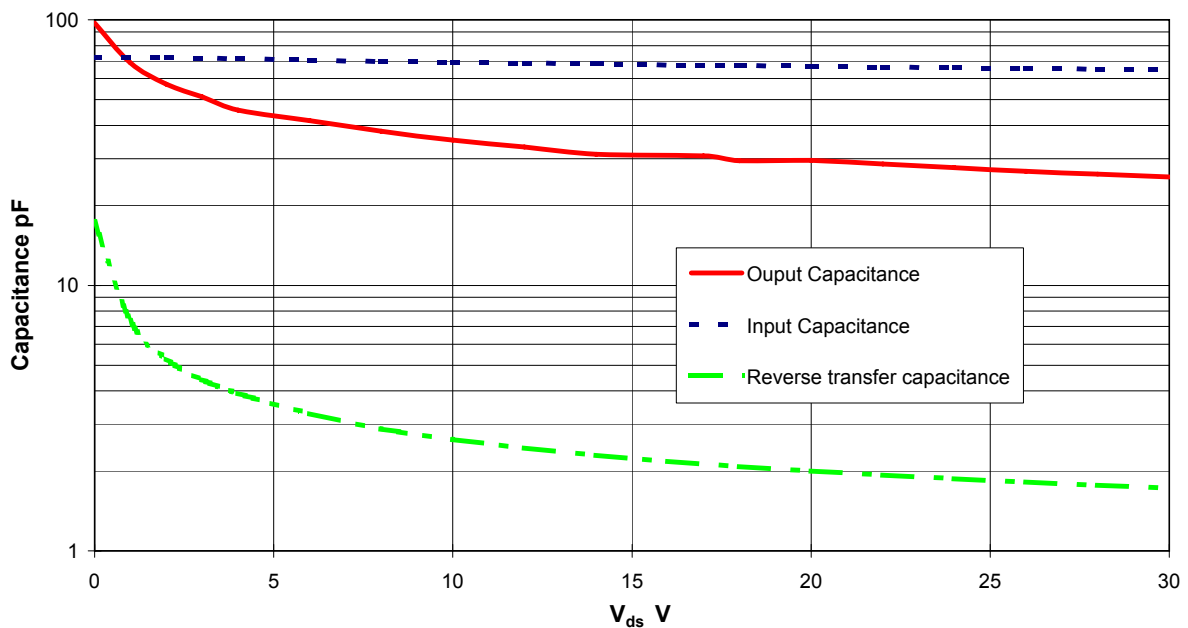
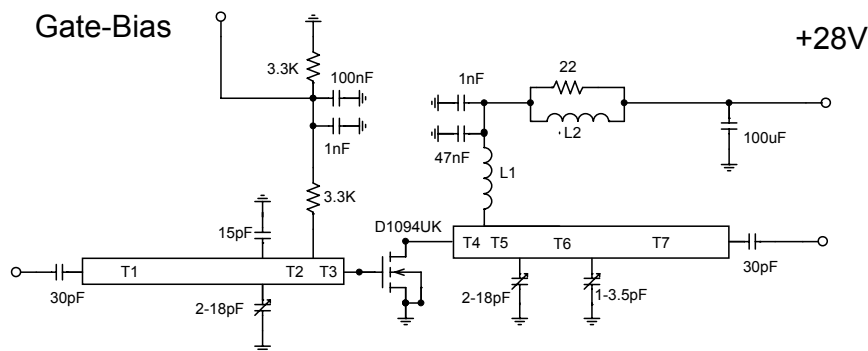


Figure 5 – Typical CV Characteristics.

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.



## D1094UK 500MHz TEST FIXTURE

Substrate 1.6mm thick G200

All microstrip lines  $W=2.8\text{mm}$

T1 46.3mm

T2 2.2mm

T3, T4 8mm

T5 4.3mm

T6 11.7mm

T7 32.3mm

L1 7 turns 24swg enamelled copper wire, 3mm i.d.

L2 1.5 turns 24swg enamelled copper wire on ferrite core